

BCD8sP Technology Overview

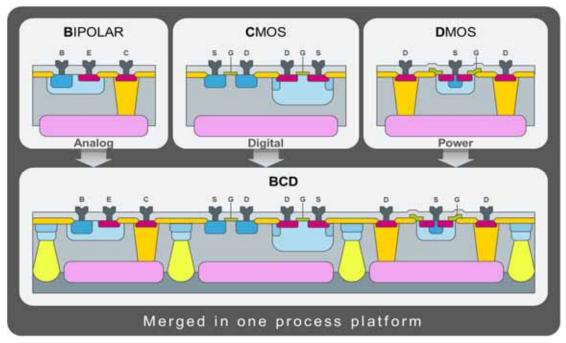
Sense & Power and Automotive Technology R&D Smart Power Technology

February 2015



What is BCD?

A concept invented by ST in the mid-80s [1][2][3] widely used today in the industry



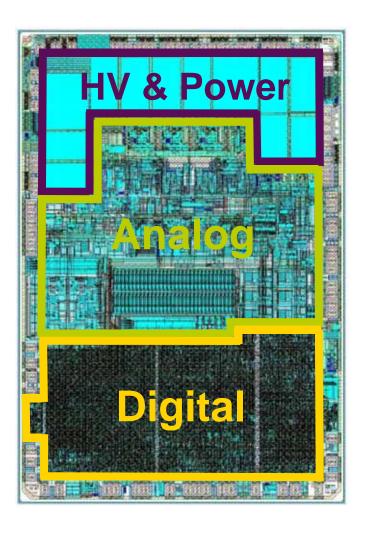
[1] Single Chip Carries Three technologies, Electronics Week, December 10, 1984

[2] C. Cini, C. Contiero, C. Diazzi, P. Galbiati, D. Rossi, "A New Bipolar, CMOS, DMOS Mixed Technology for Intelligent Power Applications", ESSDERC '85 Proceedings, Aachen (Germany), September 1985

[3] A. Andreini, C. Contiero, P. Galbiati, "A New Integrated Silicon Gate Technology Combining Bipolar Linear, CMOS Logic and DMOS Power Parts", IEEE Transactions on Electron Devices, Vol. ED-33 No.12, December 1986



Analog + Digital + Power & HV on one chip



High Voltage or Power section (DMOS) to drive external loads

Analog blocks to interface the "external world" to the digital systems

Digital core (CMOS) for signal processing



BCD Technology Segmentation

| SEGMENT | | TECHNOLOGY PLATFORM | APPLICATION FIELDS | | |
|------------------------|--------|--|-----------------------------|-----------------|-----------------------------|
| High Voltage BCD | | BCD6s Offline 3.3V / 5V CMOS – 25V/800V | E Lighting | ⊮ Motors | Electrical Car |
| | 0.32µm | BCD6s HV Transformer 3.3V CMOS - Galvanic Isolation 4-6KV | | | |
| SOI | | SOI-BCD6s 3.3V CMOS - 20V/50V/100V/190V | _1)) | 5 | |
| BCD | | SOI-BCD8s 1.8V CMOS - 70V/100V/140V/200V | Full digital amplifier | Echography | AMOLED Pico-projector |
| | 0.16µm | BCD8As 3.3V CMOS - 8V/18V/40V | | 02 | |
| | | BCD8sP 1.8V CMOS - 10V/18V/27V/42V/60V | HDD | Airbag 🛕 | Audio amplifier |
| Advanced | | BCD8sAUTO 3.3V CMOS - 20V/40V/65V/100V | | ESP | |
| BCD | шm | BCD9s 1.8V CMOS - 10V/40V/60V | Printers (| ABS) | Power Line modems |
| | 0.11 | BCD9sL 3.3V CMOS - 20V/40V/65V/100V | | | |
| | 90nm | BCD10 1.2V CMOS - 8V to 65V | Power Supply | Automotive | Power Management for Mobile |
| High | 0.18µm | HVG8 1.8V/22V/32V CMOS | Bio Medical Advanced Analog | | ↑ |
| Voltage CMOS | 0.18 | HVG8A 16V CMOS | | | dvanced Analog |



BCD Evolution in the "More than Moore" arena



Driven more by Process Customization for Application Requirements than by Reduction of Lithography Node



Trend towards Advanced Technology Nodes compatible with availability of Depreciated Advanced Manufacturing Plants



Long Lifetime of Products and Process Generations



Always present demand for Cost Reduction



BCD in ST – Overview

Solid know-how developed over three decades

 Processes from 4.0 µm to 0.11 µm developed and produced

Unique voltage range offering

5 V to

Large voltage range spanning multiple application fields

800 V

 Advanced process nodes differentiated by application

 $0.16 \mu m$

 Offers best in class HV devices with large CMOS integration capability

- Process customization by application
 - Strong synergy between technology, design and application









BCD8sP Overview ____

BCD8sP is a 0.16µm Technology Platform dedicated to Smart Power applications with the following main features:

- Baseline 1.8V CMOS for High Density Logic cores
- Best-in-class Power devices: 10V 18V 27V 42V
- Dual gate oxide process: 1.8V CMOS, 5V CMOS & Power Devices
- 4 Metal Levels with Thick Power metal.
- Available memory: OTP, FTP (EEPROM)

Application examples:

- Hard Disk Drivers Power Combo
- Motor Drivers
- Printer
- DC-DC converter
- Power Management





BCD8sP Device Portfolio

Low Voltage

- **1.8V CMOS**
- **5V CMOS**

Diodes

- 5V Zener, 5V Isolated Zener
- p+/Nwell, p+/HVnwell
- n+/Pwell, n+/Hvpwell

High Voltage

- 10V/18V/27V/42V Power **NMOS** Isolated Drain
- 42V Power NMOS HS
- 15V/27V/32V/48V/60V nDrift MOS
- 15V/27V/32V/48V/60V pDrift MOS

Capacitors

- 1.8V/5V poly capacitors
- 12V poly-poly capacitor
- MOM

Resistors

- Poly resistors (4 types), including HIPO resistor
- · Diffused resistor

Bipolars

- 5V NPN
- 5V PNP HP (Isolated Vertical)
- 18V PNP (Isolated Vertical)

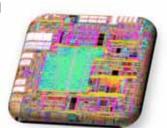
ESD & IPs

- 1.8V/5V/8V/18V/42V/60V **ESD** protection
- OTP & NVM libraries



BCD8sP Main Features

- 1.8V CMOS with HD Digital Library (90 kGates/mm²)
- 5V CMOS and wide passive components offer for Analog design
- 4 Metal level BEOL with following options for Top Metal:
 - 3µm Thick Aluminum
 - 10µm Thick Copper (Re-Distribution Layer)

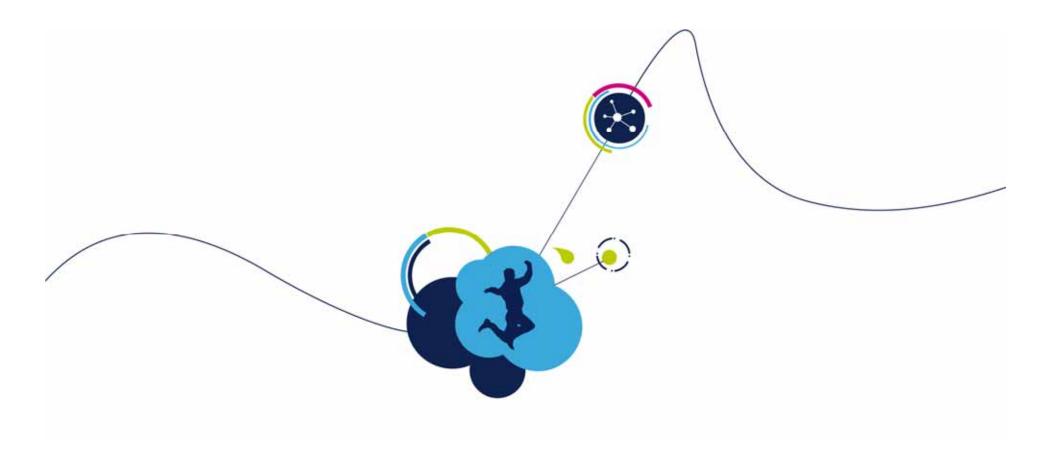


Best-in-class Power devices with specification matching real application needs

| Nch MOS POWER S | POWER PERFORMANCE | | |
|-----------------------------|---------------------------|----------------|---|
| (full T range: -40 ° | (T = 25 ° C) | | |
| Max Operating Voltage (MOV) | Absolute Max Rating (AMR) | BVdss (TYP) | $R_{ON} \times A$ (m $\Omega \times mm^2$) |
| 10 V | 12 V | 14 V | 2.9 |
| 18 V | 25 V | 29 V | 8.7 |
| 27 V | 32 V | 36 V | 14.2 |
| 42 V | 46 V | 57 V | 28 |

Typical product masks count (based on option): 28 to 33





Design Platform: Design Kit, supported tools & Libraries



Design Platform – Basic Tools Supported in PDK 11

| Front-end/Schematic capture | EDA tools | EDA Vendors | Tool version (or newest) |
|------------------------------|-----------|----------------|--------------------------|
| Schematic Capture (Composer) | IC | Cadence | IC6.1.6.500.3 |
| Design environment | ArtistKit | ST | 5.9 |
| | Spectre | Cadence | 12.11.164 |
| | Eldo | Mentor | 13.1 |

| Layout Entry & Finishing | EDA tools | EDA Vendors | Tool version (or newest) |
|---------------------------------------|---------------------------|-------------------|---------------------------|
| Layout Placement | Virtuoso Layout Editor | Cadence | IC6.1.6.500.3 |
| Layout Verification | Calibre ViPVS | Mentor Cadence | 2013.1_14.11 13.10.286 |
| Parasitic Extraction: interconnect RC | Star-RCXT | Synopsys | i-2013.12-1 |

Metal options available: 4M AI - 4M Cu RDL



Design Platform – Full List of supported Tools

Cadence

IC 6.1.6.500.3 (Virtuoso Framework)
Spectre 12.11.164 (Analog Simulator)
ViPVS 13.10.286 (Layout Verification)
mmsim 12.11.164 (Analog simulator environment)
incisiv 13.10.001 (Simulation Verification Environment)
Conformal 12.10.300 (Formal Verification)
Rc 12.20.000 (Synthesis)
edi 13.2usr3 (P&R)
IC 6.1.6.500.3 (VSR AnalogRouter)

Synopsys

Star-RCXT i-2013.12-1 (Parasitic Extraction hsimplus i-2013.12 (Tx Level Simulator) mvtools g-2012.09-4 (Static checker) vcsmx h-2013.06-sp1 (Digitla simulator) xa i-2013.12 (Tx Level Simulator) Primetime h-2013.06-sp2 (STA) PrimeRail f2011.12 (Digital IRDrop) Synthesis h-2013.03-sp3 (ATPG) Formality h-2013.03-sp3 (Formal Check) Galaxy-ca h-2013.06-sp2 (Constraint Analyzer) Iccompiler g-2012.06-sp5 (P&R)

Hercules y-2006.12-sp2-6 (Cheker for Prme Rail)

Mentor

Eldo/Eldo Premier 13.1 (transistor level)
Questa-ADMS 13.1 (mixed-signal cosimulation)
Calibre 2013.1_14.11 (Layout Verification)
QuestaSim 10.2.b (digital simulation)



Design Platform – Digital Libraries/IPs 13

Digital Library

BCD8000HDS - (1.8V CMOS)

SP Analog **IPs**

Macrocells ESD

Dedicated library for HV protection

Memory **Compilers**

- Single port RAM (2 compilers)
- OTP (1 to 16) x (8/16) bits
- · Cut service available on request

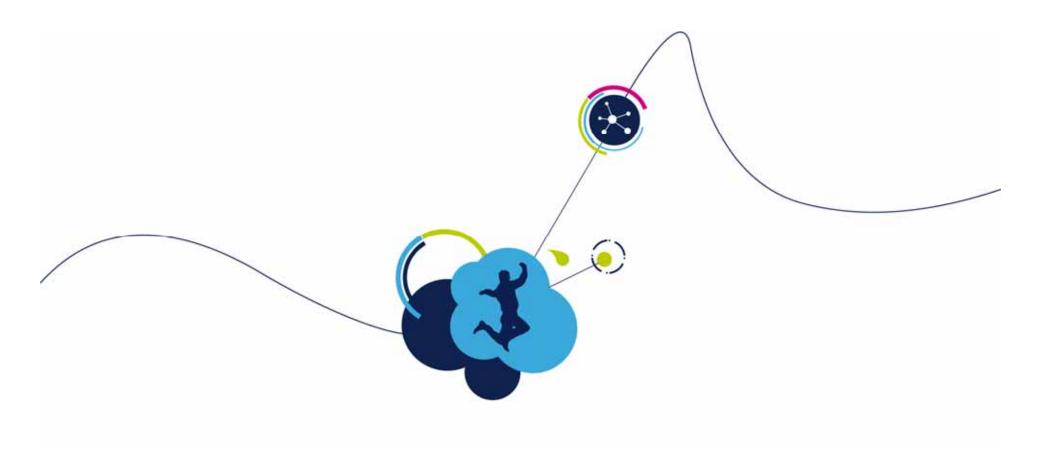
10's Libraries

- 3V3FT 4MAI (3V capable 5V tolerant GPIO)
- 5V0 4MAI (5V capable GPIO)

Power **Devices** Library

- «Ready-to-use» Power Devices layout
- Cut service available on request





Schedule



BCD8sP Design Timeline

PDK / Design Platform availability

NOW

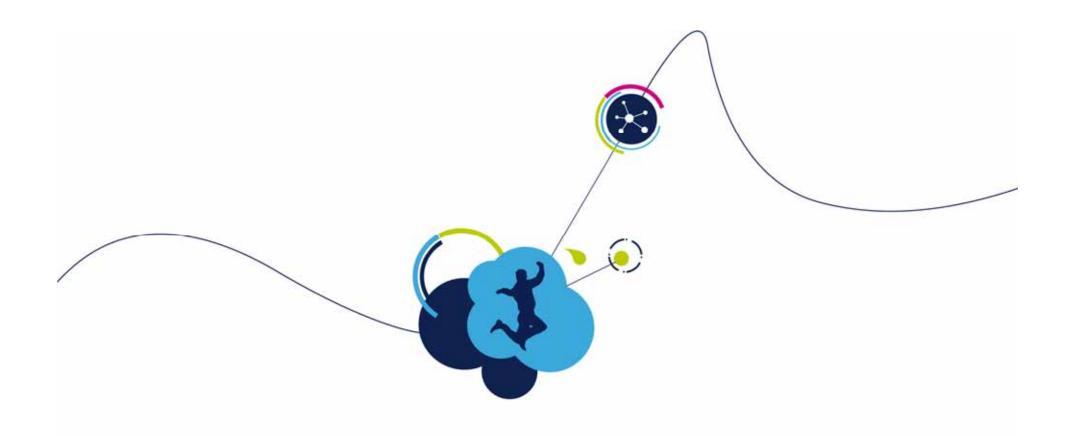
Next MPW run

June 2015

Last MPW in 2015

November 2015





Thank You

